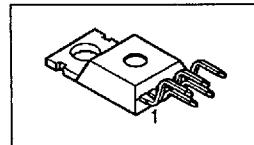


## PROFET®

- High-side switch
- Short-circuit protection
- Overtemperature protection
- Overload protection
- Load dump protection<sup>1)</sup>
- Undervoltage and overvoltage shutdown with auto-restart and hysteresis
- Reverse battery protection<sup>1)</sup>
- Input and status protection
- Clamp of negative output voltage with inductive loads
- Protection against charged inductive load disconnect<sup>2)</sup>
- Open load detection in ON-state
- Maximum current internally limited
- Status output for load fault
- $R_{ON}$  constant versus  $V_{bb}$
- Electrostatic Discharge (ESD) protection

Version differences see truth table and options overview, page 20...21

Package: TO220AB/5 (mounting flange is shorted to pin 3),  
different package outlines (see page 28) on request



## Ordering codes and packages see page 28

Pins				
1	2	3	4	5
GND	IN	$V_{bb}$	ST	OUT
-	I	+	S	O (Load,L)

## Maximum Ratings

Parameter	Symbol	Values	Unit
Active overvoltage protection	$V_{bb(AZ)}$	> 50	V
Load current (Short-circuit current, see page 19)	$I_L$	self-limited	A
Operating temperature range	$T_J$	-40 ...+150	°C
Storage temperature range	$T_{stg}$	-55 ...+150	
Max. power dissipation	$P_{tot}$	75	W
Maximum current through input pin (DC)	$I_{IN}$	$\pm 2.0$	mA
Maximum current through status pin (DC) see internal circuit diagram see chapter 2	$I_{ST}$	$\pm 5.0$	
Thermal resistance chip - case	$R_{thJC}$	1.67	K/W
chip - ambient:	$R_{thJA}$	75	

1) with resistor  $R_{GND}=150 \Omega$  in GND connection, 15 k $\Omega$  resistor in series with IN and ST connections, reverse load current limited by connected load.

2) with 150  $\Omega$  resistor in GND connection or freewheeling diode between  $V_{bb}$  and GND or freewheeling diode parallel to load. To protect against  $V_{bb}$  loss with an inductive load, it is recommended that a freewheeling diode be added between  $V_{bb}$  and GND.

**Electrical Characteristics**

Parameter and Conditions at $T_J = 25^\circ\text{C}$ , $V_{bb} = 12\text{V}$ unless otherwise specified	Symbol	Values			Unit
		min	typ	max	

**Load Switching Capabilities and Characteristics**

On-state resistance (pin 3 to 5) $I_L = 1\text{ A}$ , $V_{IN}=\text{high}$	$T_J=25^\circ\text{C}$ : $T_J=150^\circ\text{C}$ :	$R_{ON}$	--	190 390	220 440	$\text{m}\Omega$
Nominal load current (pin 3 to 5) ISO Proposal: $V_{bb} - V_{OUT} \leq 0.5\text{ V}$ , $T_C = 85^\circ\text{C}$		$I_{L(\text{ISO})}$	1.6	--	--	A
Open load detection current	$T_J=25..150^\circ\text{C}$ : $T_J=-40^\circ\text{C}$ :	$I_{L(\text{OL})}$	2 2	-- --	150 200	$\text{mA}$
Turn-on time	to 90% $V_{OUT}$	$t_{on}$	15	--	60	$\mu\text{s}$
Turn-off time	to 10% $V_{OUT}$	$t_{off}$	5	--	50	
$R_L = 12\Omega$						
Slew rate on 10 to 30% $V_{OUT}$ , $R_L = 12\Omega$		$dV/dt_{on}$	--	--	3	$\text{V}/\mu\text{s}$
Slew rate off 70 to 40% $V_{OUT}$ , $R_L = 12\Omega$		$-dV/dt_{off}$	--	--	5	
Standby current (pin 3) $V_{IN}=0$ , $I_{ST}=0$	$T_J=150^\circ\text{C}$ :	$I_{bb(\text{off})}$	--	12 18	25 60	$\mu\text{A}$
Operating current (Pin 1), $V_{IN}=\text{high}$		$I_{GND}$	--	2.2 <sup>3)</sup>	--	$\text{mA}$
Short circuit shutdown delay after input pos. slope $T_J=-40..+150^\circ\text{C}$ : $V_{bb}-V_{OUT}=V_{ON} > V_{ON(\text{SC})}$ (see page 19) min value valid only, if input "low" time exceeds 60 $\mu\text{s}$		$t_d(\text{SC})$	80	--	350	$\mu\text{s}$

**Input and Status Feedback<sup>4)</sup>**

Allowable input voltage range, (pin 2 to 1)	$V_{IN}$	-0.5	--	5.5	V	
Input turn-on threshold voltage	$V_{IN(T+)}$	1.5	--	2.4	V	
Input turn-off threshold voltage	$V_{IN(T-)}$	0.8	--	--	V	
Input threshold hysteresis	$\Delta V_{IN(T)}$	--	0.5	--	V	
Off state input current (pin 2)	$V_{IN(\text{off})} = 0.4\text{ V}$	$I_{IN(\text{off})}$	1	--	30	$\mu\text{A}$
On state input current (pin 2)	$V_{IN(\text{on})} = 3.5\text{ V}$	$I_{IN(\text{on})}$	10	25	70	
Delay time for status with open load (see timing diagrams, page 27)		$t_d(ST\text{OL1})$	--	700	--	$\mu\text{s}$
		$t_d(ST\text{OL2})$	--	200	--	
Status valid after input slope $T_J=-40 \dots +150^\circ\text{C}$ : (short circuit, open load)		$t_d(ST)$	80	--	350	$\mu\text{s}$

<sup>3)</sup> see diagram page 25, Add  $I_{ST}$ , if  $I_{ST} > 0$ <sup>4)</sup> if a ground resistor  $R_{GND}$  is used, add the voltage across this resistor. Internal Z-diode typ. 6.1 V, see maximum ratings page 17, (see chapter 3)

Parameter and Conditions at $T_j = 25^\circ\text{C}$ , $V_{bb} = 12\text{V}$ unless otherwise specified	Symbol	Values			Unit
		min	typ	max	
Status output (CMOS)					
$T_j = -40 \dots +150^\circ\text{C}$ , $I_{ST} = -50\ \mu\text{A}$ :	$V_{ST(\text{high})}$ <sup>6)</sup>	4.4	5.1	6.5	V
$T_j = -40 \dots +25^\circ\text{C}$ , $I_{ST} = +1.6\text{ mA}$ :	$V_{ST(\text{low})}$	--	--	0.8	
$T_j = +150^\circ\text{C}$ , $I_{ST} = +1.6\text{ mA}$ :		--	--	1.0	
Max. status current for valid status output, $T_j = -40 \dots +150^\circ\text{C}$	$-I_{ST}$	--	--	0.25	mA
	$+I_{ST}$	--	--	1.6	

**Operating and Clamp Voltages**

Operating voltage	$T_j = 25^\circ\text{C}$ : $T_j = -40 \dots +150^\circ\text{C}$ :	$V_{bb(\text{on})}$	4.9 5.8	--	42 40	V
Undervoltage shutdown	$T_j = 25 \dots +150^\circ\text{C}$ : $T_j = -40^\circ\text{C}$ :	$V_{bb(\text{under})}$	2.4 3.0	--	4.9 5.4	
Undervoltage restart	$T_j = 25 \dots +150^\circ\text{C}$ : $T_j = -40^\circ\text{C}$ :	$V_{bb(u\ rst)}$	-- --	--	4.9 5.8	
Oversupply shutdown	$T_j = -40 \dots +150^\circ\text{C}$ :	$V_{bb(\text{over})}$	42	--	52	
Oversupply restart	$T_j = -40 \dots +150^\circ\text{C}$ :	$V_{bb(o\ rst)}$	40	--	--	
Oversupply protection	$T_j = -40 \dots +150^\circ\text{C}$ :	$V_{bb(AZ)}$	50	56	--	
Load dump protection <sup>7)</sup>		$V_{bb(LD)}$	--	--	93.5	
Output clamp (inductive load switch off)		$-V_{OUT(CL)}$	--	10	--	
Short circuit shutdown detection voltage (pin 3 to 5)		$V_{ON(SC)}$	--	8.6	10	

**Protection Functions**

Overload current limit (pin 3 to 5), after 200 ms, $V_{ON} = 8\text{ V}$ , no heatsink <sup>8)</sup> , see diagram page 23						
$T_j = -40 \dots +150^\circ\text{C}$	$I_L(\text{lim})$	3.1	11	21	A	
Thermal overload trip temperature	$T_{jt}$	150	--	--	°C	
Inductive load switch-off energy dissipation <sup>9)</sup> , $T_{j,\text{start}} = 150^\circ\text{C}$ , $V_{bb} = 12\text{V}$ $E_{\text{Load}} = \frac{1}{2} * L * I_L^2$	$E_{ab}$ $E_{\text{Load12}}$ $E_{\text{Load24}}$	-- --	--	1.4 0.6 0.4	J	
$V_{bb} = 12\text{V}$ $V_{bb} = 24\text{V}$						
Reverse battery (pin 1 to 3) <sup>10)</sup>	$-V_{bb}$	--	--	32	V	

5) no current sink capability during undervoltage shutdown

6)  $V_{St\ high} \approx V_{bb}$  during undervoltage shutdown7) Requires  $150\ \Omega$  resistor in GND connection. Input and Status currents have to be limited. It is recommended that  $15k\Omega$  resistors be inserted in series with IN and ST.8) this occurs, if circuit resistance is so high, that no short circuit shutdown occurs ( $V_{ON} < V_{ON(SC)}$ )9) while demagnetizing load inductance, dissipated energy in PROFET is  $E_{ab} = \int (V_{bb} + |V_{OUT(CL)}|) * i_L(t) dt$ ,  
approx.  $E_{ab} = \frac{1}{2} * L * I_L^2 * (1 + \frac{V_{bb}}{|V_{OUT(CL)}|})$ 10) Requires  $150\ \Omega$  resistor in GND connection. Reverse load current (through intrinsic drain-source diode) is normally limited by the connected load. Reverse current  $I_{GND}$  of about 0.4 A at  $V_{bb} = -32\text{V}$  through the logic (see chapter 3) heats up the device. Time allowed under these condition is dependent on the size of the heatsink. Input and Status currents have to be limited. It is recommended that  $15k\Omega$  resistors be inserted in series with IN and ST.

## Truth Table

	Input-level	Output level	Status				
			version 412 B	version D	version E/F	version G	version H
Normal operation	L	L	H	H	H	H	H
	H	H	H	H	H	H	H
Open load	L	<sup>11)</sup>	L	H	H	H	L
	H		H	L	L	L	H
Short circuit to GND	L	L	H	H	H	H	H
	H	L	L	L	L	H	L
Short circuit to V <sub>bb</sub>	L	H	L	H	H	H	L
	H	H	H	H (L <sup>12)</sup> )	H (L <sup>12)</sup> )	H (L <sup>12)</sup> )	H
Overtemperature	L	L	L	L	L	L	L
	H	L	L	L	L	L	L
Undervoltage	L	L	L <sup>13)</sup>	L <sup>13)</sup>	H	H	H
	H	L	L <sup>13)</sup>	L <sup>13)</sup>	H	H	H
Oversupply	L	L	L	L	H	H	H
	H	L	L	L	H	H	H

L = "Low" Level

H = "High" Level

<sup>11)</sup> Power Transistor off, high impedance, versions BTS 410H, BTS 412B:  
source for open load detection.

internal pull up current

<sup>12)</sup> low resistance to V<sub>bb</sub> may be detected by no-load-detection

<sup>13)</sup> no current sink capability during undervoltage shutdown

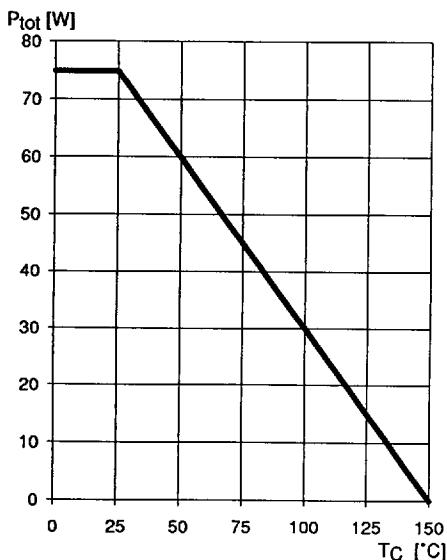
## Options Overview

all versions: High-side switch, Input protection, ESD protection, load dump and reverse battery protection with  $150 \Omega$  in GND connection

Type	BTS	412 B	410D	410E	410F	410G	410H
Logic version		B	D	E	F	G	H
Overtemperature protection $T_j > 150^\circ\text{C}$ , latch function <sup>14)</sup>	X	X		X		X	
$T_j > 150^\circ\text{C}$ , with auto-restart on cooling			X		X		
Short-circuit to GND protection switches off when $V_{bb} - V_{OUT} > 3.5 \text{ V typ.}$ (when first turned on after approx. 150 $\mu\text{s}$ )	X	X	X	X			X
switches off when $V_{bb} - V_{OUT} > 8.6 \text{ V typ.}$ (when first turned on after approx. 150 $\mu\text{s}$ )						X	
Achieved through overtemperature protection						X	
Open load detection in OFF-state with sensing current 30 $\mu\text{A typ.}$ in ON-state with sensing voltage drop across power transistor	X		X	X	X	X	X
Undervoltage shutdown with auto restart	X	X	X	X	X	X	X
Oversupply shutdown with auto restart	X	X	X	X	X	X	X
Status feedback for overtemperature	X	X	X	X	X	X	X
short circuit to GND	X	X	X	X			X
short to $V_{bb}$	X						X
open load	X	X	X	X	X	X	X
undervoltage, oversupply	X	X					
Status output type CMOS	X	X		X	X	X	X
Open drain							
Output negative voltage transient limit (fast inductive load switch off) to -10 V typ	X	X	X	X	X	X	X
Load current limit high level (can handle loads with high inrush currents) low level (better protection of application)	X	X	X		X	X	X

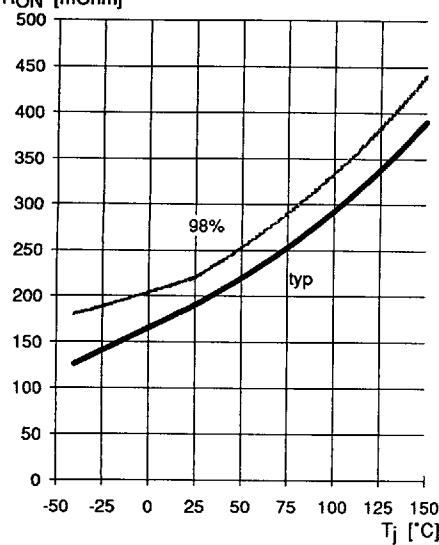
<sup>14)</sup> Latch except when  $V_{bb} - V_{OUT} < V_{ON(SC)}$  after shutdown. In most cases  $V_{OUT} = 0 \text{ V}$  after shutdown ( $V_{OUT} \neq 0 \text{ V}$  only if forced externally). So the device remains latched unless  $V_{bb} < V_{ON(SC)}$  (see page 19). No latch between turn on and  $t_d(SC)$ .

**Maximum allowable power dissipation**  
 $P_{tot} = f(T_C)$



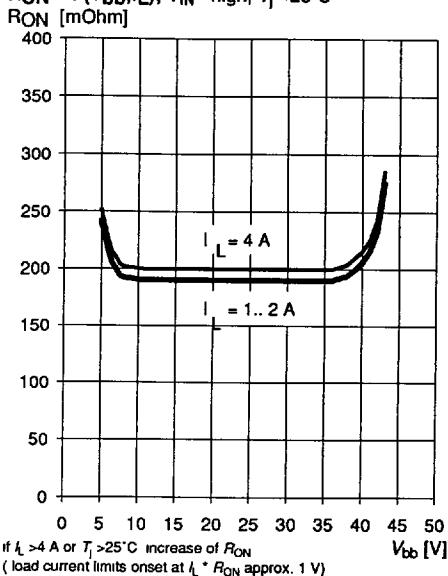
**On-state resistance (V<sub>bb</sub>-Pin to OUT-Pin)**

$R_{ON} = f(T_j)$ ;  $V_{bb} = 9..35\text{V}$ ;  $I_L = 1\text{ A}$ ;  $V_{IN} = \text{high}$   
 $R_{ON}$  [mOhm]



**Typ. on-state resistance (V<sub>bb</sub>-Pin to OUT-Pin)**

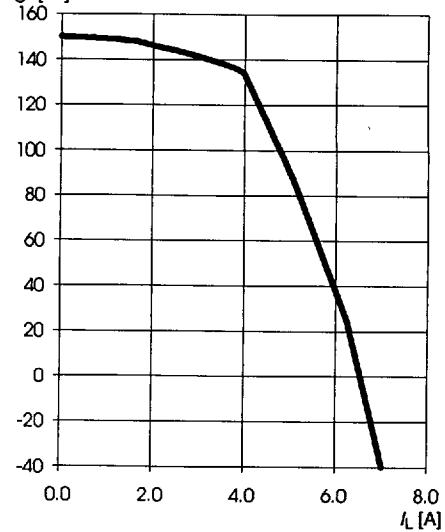
$R_{ON} = f(V_{bb}, I_L)$ ;  $V_{IN} = \text{high}$ ,  $T_j = 25^\circ\text{C}$



**Max. case temperature vs DC load current**

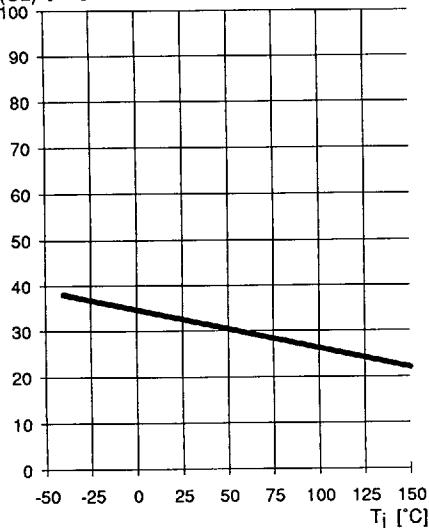
$T_C \text{ max} = f(I_L)$

$T_C [^\circ\text{C}]$



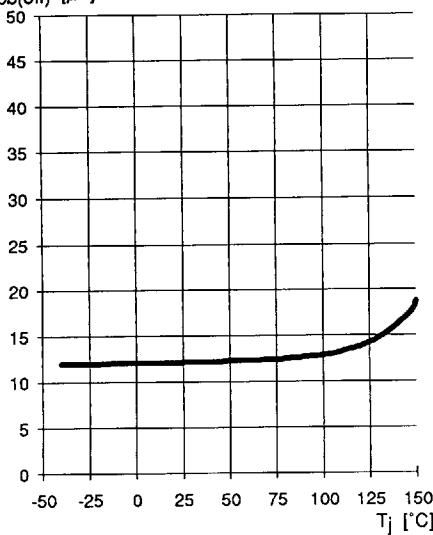
## Typ. open load detect current

$I_{L(OL)} = f(T_j)$ ;  $V_{bb} = 9...35$  V;  $V_{IN}$  = high  
 $I_{L(OL)}$  [mA]



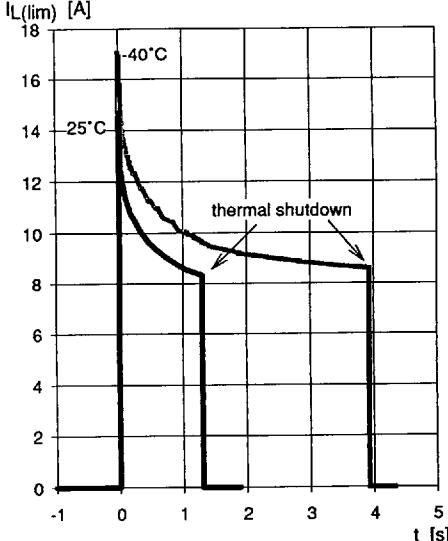
## Typ. standby current

$I_{bb(off)} = f(T_j)$ ,  $V_{bb} = 9...35$  V,  $V_{IN}$  = low  
 $I_{bb(off)}$  [ $\mu$ A]



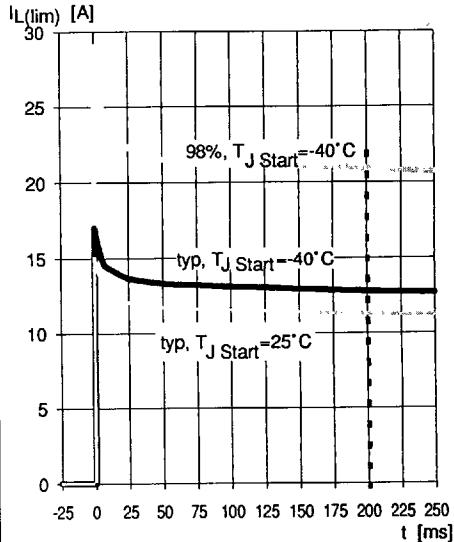
## Typ. overload current

$I_{L(lim)} = f(t)$ ;  $V_{bb} = 12$  V,  $V_{bb} - V_{OUT} = 8$  V,  
no heatsink, Parameter:  $T_j$  Start



## Overload Current

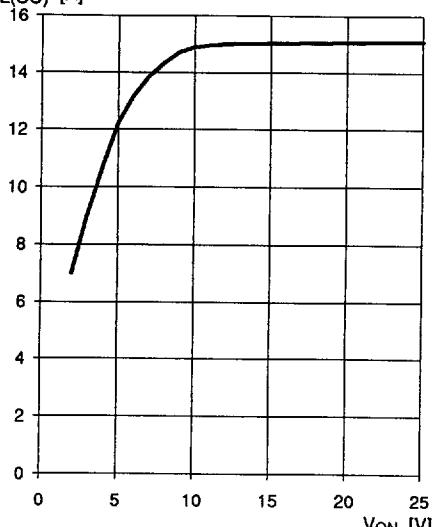
$I_{L(lim)} = f(t)$ ;  $V_{bb} = 12$  V,  $V_{bb} - V_{OUT} = 8$  V,  
no heatsink



**Typ. short circuit Current**

$$I_{L(SC)} = f(V_{ON}) ; \quad T_j = 25^\circ\text{C}$$

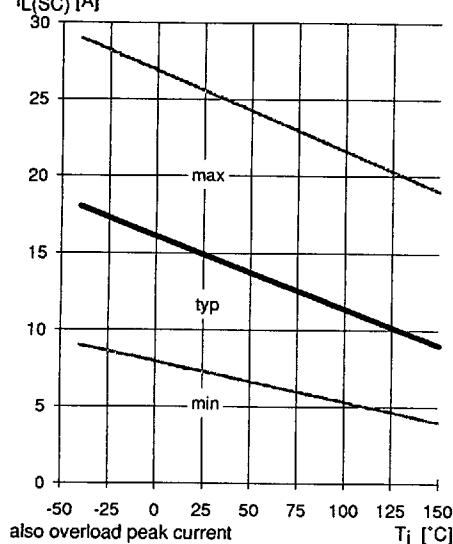
$$I_{L(SC)} [\text{A}]$$

**Short circuit current**

max duration 350  $\mu\text{s}$  prior to shutdown

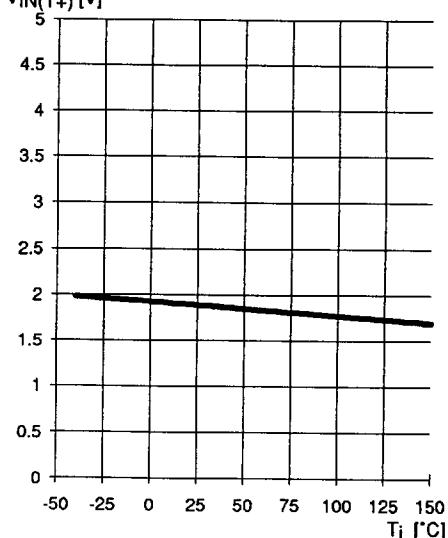
$$I_{L(SC)} = f(T_j) ; \quad V_{bb} = 12 \dots 35 \text{ V} ; \quad V_{IN} = \text{High}$$

$$I_{L(SC)} [\text{A}]$$

**Typ. input turn on voltage threshold**

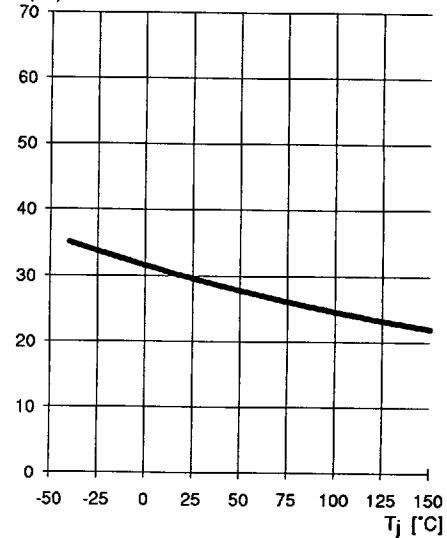
$$V_{IN(T+)} = f(T_j) ; \quad V_{bb} = 9 \dots 35 \text{ V}$$

$$V_{IN(T+)} [\text{V}]$$

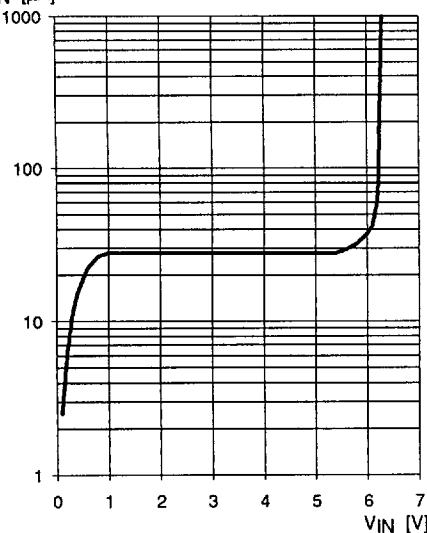
**Typ. input current high**

$$|I_{IN(on)}| = f(T_j) ; \quad V_{IN} = 3.5 \dots 5.5 \text{ V}$$

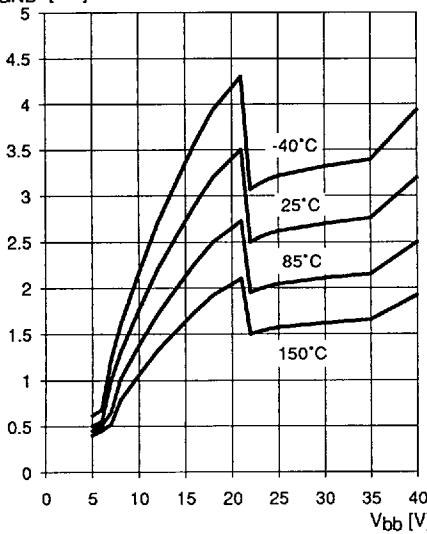
$$|I_{IN(on)}| [\mu\text{A}]$$



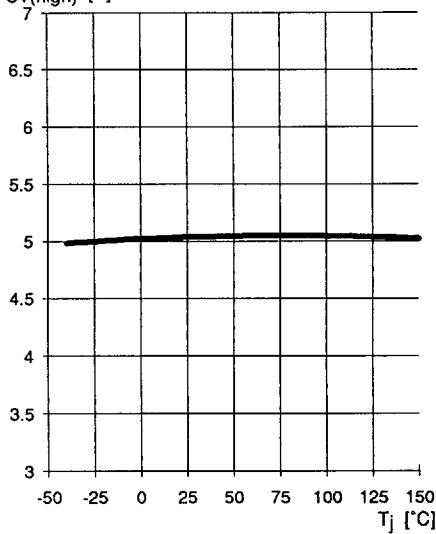
## Typ. input current

 $I_{IN} = f(V_{IN})$ ,  $V_{bb} = 9 \dots 35V$ ,  $T_j = 25^\circ C$  $I_{IN}$  [ $\mu A$ ]

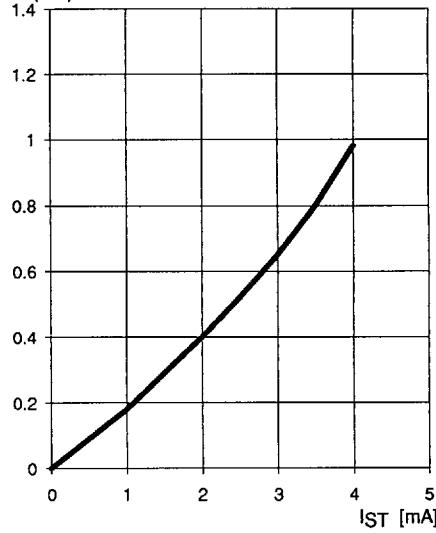
## Typ. ground pin operating current

 $I_{GND} = f(V_{bb}, T_j)$ ;  $V_{IN} = \text{high}$  $I_{GND}$  [mA]

## Typ. status high voltage

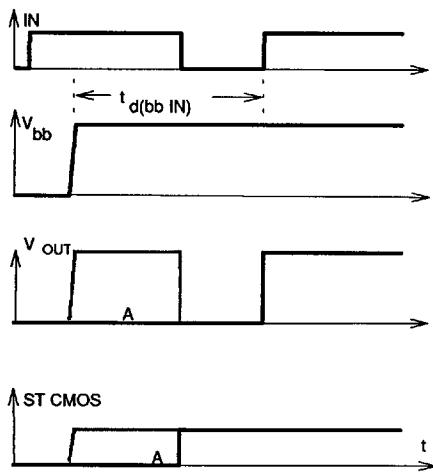
 $V_{ST(\text{high})} = f(T_j)$ ;  $V_{bb} = 12V \dots 35V$  $V_{ST(\text{high})}$  [V]

## Typ. status low voltage

 $V_{ST(\text{low})} = f(I_{ST})$ ,  $V_{bb} = 9 \dots 35V$ ,  $T_j = 25^\circ C$  $V_{ST(\text{low})}$  [V]

## Timing diagrams

Figure 1a:  $V_{bb}$  turn on:



in case of too early  $V_{IN}$ =high the device may not turn on (curve A)  
 $t_{d(bb\ IN)}$  approx. 150  $\mu$ s

Figure 2a: Switching a lamp,

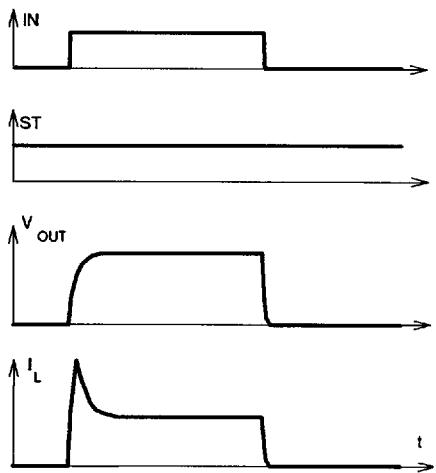
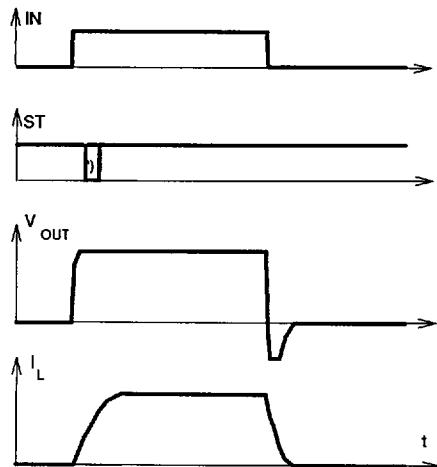


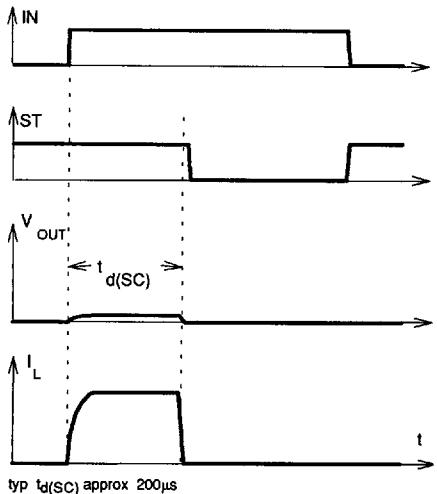
Figure 2b: Switching an inductive load,

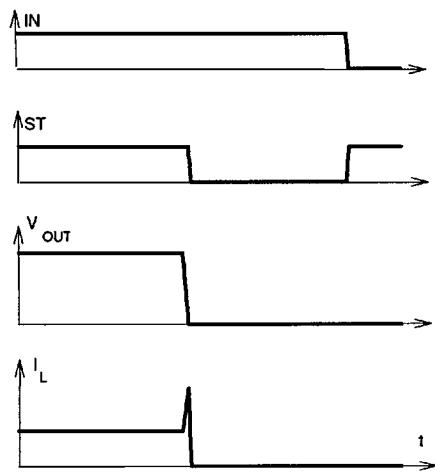
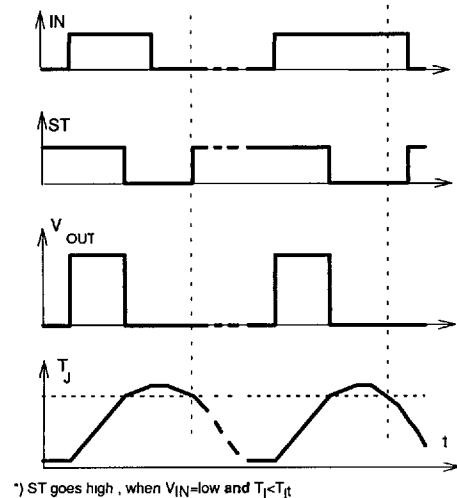
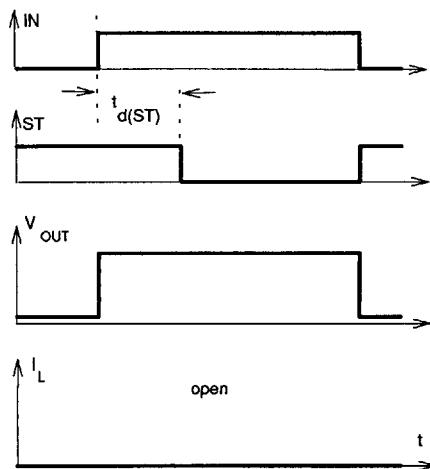
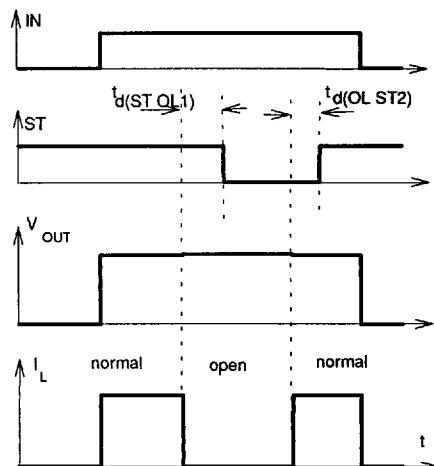
(Better protection of application: versions BTS 410 F/G/H)



\*) if the time constant of load is too large, open-load-status may occur

Figure 3a: turn on into short circuit,

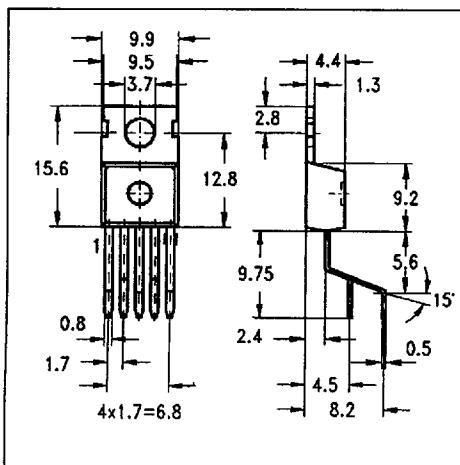


**Figure 3b:** short circuit while on:**Figure 4a:** overtemperature,Reset if (IN=low) and ( $T_J < T_{Jt}$ )\*) ST goes high , when  $V_{IN}=\text{low}$  and  $T_J < T_{Jt}$ **Figure 5a:** open load: detection in ON-state, turn on to open load**Figure 5b:** open load: detection in ON-state, open load occurs in on-state

Package and ordering code

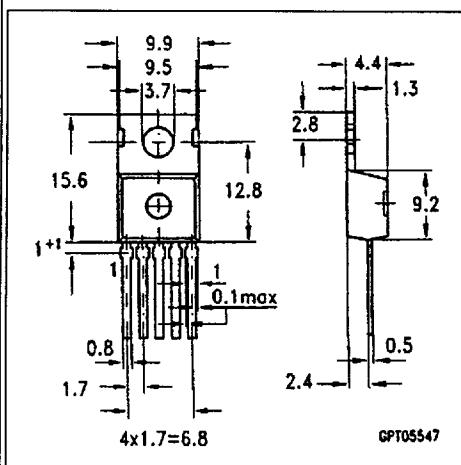
## Standard

BTS 410 D	C67078-S5305-A3
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## E3043

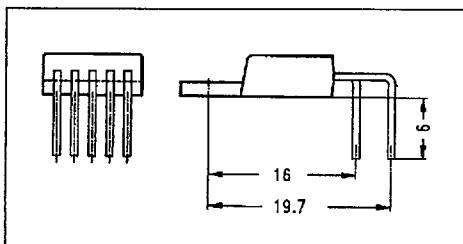
BTS 410 D	C67078-S5305-A20
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GPT05547

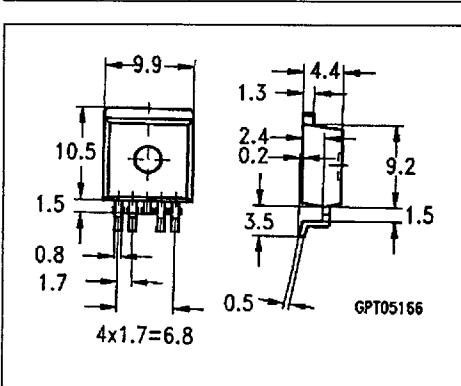
## E3040

BTS 410 D	C67078-S5305-A7
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## SMD

BTS 410 D E3062	Tube: C67078-S5305-A11
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GPT05166

SMD

BTS 410 D E3122

Tube: C67078-S5305-A15

